

a portion [having substantially consistent reactivity] being substantially non-reactive to the process chemistry used in the semiconductor fabrication apparatus over the entire operating life of the gas distribution plate.

2. (Once Amended) A gas distribution plate as recited in claim 1 wherein the portion of the gas distribution plate is rendered substantially non-reactive by reducing [the] surface defects on the portion before implementation within the semiconductor fabrication apparatus.

5. (Once Amended) A gas distribution plate as recited in claim 1 wherein, during its operation, the gas distribution plate [always] produces less than 0.1 defect particles per square centimeter for a wafer processed in the semiconductor fabrication apparatus over the entire operating life of the gas distribution plate.

Please ADD claims 38 and 39 as follows:

38. (New) A gas distribution plate as recited in claim 1 wherein the portion of the gas distribution plate has substantially no micro-defects that may lead to contamination of a wafer located within said semiconductor processing chamber

39. (New) A gas distribution plate as recited in claim 38 wherein the portion of the gas distribution plate has substantially no micro-defects about 50 micrometers that may lead to contamination of a wafer located within said semiconductor processing chamber.

REMARKS

Applicants affirm the election of group I, claims 1-18, to prosecute in the above-identified patent application. Claims 19-37 are cancelled without prejudice to continue prosecution of claims of same or similar scope in another application. However, Applicants respectfully traverse the restriction between groups II and III provided in the Office Action on page 2. Claim 29 recites "A method of making a